10

2

## What is claimed is:

- A field emission device (FED) comprising:
- a substrate:
- a cathode formed over the substrate:
- micro-tips having nano-sized surface features, formed on the cathode;
- a gate insulation layer with wells each of which a single micro-tip is located in, the gate insulation layer formed over the substrate: and
- a gate electrode with gates aligned with the wells such that each of the microtips is exposed through a corresponding gate, the gate electrode formed on the gate insulation layer.
- The field emission device of claim 1, wherein a resistor layer is formed over or beneath the cathode, or a resistor layers is formed over and beneath the cathode.
- 3. A method for fabricating a field emission device (FED), comprising: forming a cathode, a gate insulation layer with wells, and a gate electrode with gates on a substrate in sequence, and forming micro-tips on the cathode exposed by the wells:

forming a carbonaceous polymer layer on the gate electrode, such that the wells having the micro-tips are filled with the carbonaceous polymer layer; and

etching the carbonaceous polymer layer and the surface of the micro-tips by plasma etching using a gas mixture containing  $\mathbf{O}_2$  for the carbonaceous polymer layer, and a gas for the micro-tips, as a reaction gas, so that the micro-tips with nano-sized surface features are formed.

- The method of claim 3, wherein the carbonaceous polymer layer is formed of polyimide or photoresist.
- The method of claim 3, wherein the carbonaceous polymer layer is etched by reactive ion etching (REI).

3

3

- 6. The method of claim 5, wherein the nano-sized surface features of the micro-tips are adjusted by varying the etch rates of the carbonaceous polymer layer and the micro-tips.
- 7. The method of claim 6, wherein the etch rates are adjusted by varying the oxygen-to-the gas for the micro-chips in the reaction gas, plasma power, or plasma pressure during the etching process.
- 8. The method of claim 5, wherein the micro-tips are formed of at least one selected from the group molybdenum (Mo), tungsten (W), silicon (Si) and diamond, and the reaction gas is a gas mixture of O<sub>2</sub> and fluorine-based gas.
- The method of claim 8, wherein the reaction gas comprises CF<sub>4</sub>/O<sub>2</sub>, SF<sub>6</sub>/O<sub>2</sub>, CHF<sub>3</sub>/O<sub>2</sub>, CF<sub>4</sub>/SF<sub>6</sub>/O<sub>2</sub>, CF<sub>4</sub>/CHF<sub>3</sub>/O<sub>2</sub>, and SF<sub>6</sub>/CHF<sub>3</sub>/O<sub>2</sub>.
- 10. The method of claim 5, wherein the micro-tips are formed of at least one selected from the group molybdenum (Mo), tungsten (W), silicon (Si) and diamond, and the reaction gas is a gas mixture of O<sub>2</sub> and chlorine-based gas.
- 11. The method of claim 10, wherein the reaction gas comprises  $Cl_2/O_2$ ,  $CCl_4/O_2$ , and  $Cl_2/CCl_4/O_2$ .